**Product data sheet** 

## 1. General description

WeEn's 5th Generation Hyper Fast diode with softer recovery in a 2-lead TO220F plastic package.

### 2. Features and benefits

- Isolated plastic package
- Low leakage current
- · Low thermal resistance
- · Soft reverse recovery with low recovery current
- · Reduces switching losses in associated MOSFET or IGBT

## 3. Applications

- · Active PFC in air conditioner
- Continuous Current Mode (CCM) Power Factor Correction (PFC)
- · Half-bridge/full-bridge switched-mode power supplies

### 4. Quick reference data

Table 1. Quick reference data

| Symbol           | Parameter                           | Conditions   | Values |      |     | Unit |      |
|------------------|-------------------------------------|--|--------|------|-----|------|------|
| Absolute         | maximum rating                      |  |        |      |     |      |      |
| $V_{RRM}$        | repetitive peak reverse voltage     |  | 600    |      |     |      | V    |
| $I_{F(AV)}$      | average forward current             | $\delta$ = 0.5 ; square-wave pulse; $T_h \le 51$ °C;<br>Fig. 1; Fig. 2; Fig. 3                                     | 30     |      |     |      | А    |
| I <sub>FRM</sub> | repetitive peak forward current     | $\delta$ = 0.5 ; $t_p$ = 25 μs; $T_h \le$ 51 °C; square-wave pulse   | 60     |      |     | А    |      |
| I <sub>FSM</sub> | non-repetitive peak forward current | $t_p$ = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse;<br>Fig. 4   | 260    |      | А   |      |      |
|                  |                                     | $t_p$ = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse   | 286    |      | Α   |      |      |
| Symbol           | Parameter                           | Conditions   | N      | /lin | Тур | Max  | Unit |
| Static ch        | aracteristics                       |  |        |      |     |      |      |
| V <sub>F</sub>   | forward voltage                     | I <sub>F</sub> = 30 A; T <sub>j</sub> = 25 °C; <u>Fig. 6</u>   | -      |      | 2   | 2.75 | V    |
|                  |                                     | I <sub>F</sub> = 30 A; T <sub>j</sub> = 150 °C; <u>Fig. 6</u>  | -      |      | 1.5 | 2    | V    |
| Dynamic          | characteristics                     |  | '      |      | ,   |      |      |
| t <sub>rr</sub>  | reverse recovery time               | $I_F = 1 \text{ A}$ ; $V_R = 30 \text{ V}$ ; $dI_F/dt = 50 \text{ A}/\mu\text{s}$ ; $T_j = 25 \text{ °C}$ ; Fig. 7 | -      |      | -   | 45   | ns   |

# 5. Pinning information

#### **Table 2. Pinning information**

| Pin | Symbol | Description             | Simplified outline | Graphic symbol |
|-----|--------|-------------------------|--------------------|----------------|
| 1   | K      | cathode                 | mb mb              |                |
| 2   | A      | anode                   |                    | K —            |
| mb  | n.c.   | mounting base; isolated | O                  | 001aaa020      |

# 6. Ordering information

### **Table 3. Ordering information**

| Type number  | Package<br>Name | Orderable part number | Packing method | Small packing quantity | Package version | Package issue date |
|--------------|-----------------|-----------------------|----------------|------------------------|-----------------|--------------------|
| BYC30X-600PS | TO220F-2L       | BYC30X-600PSQ         | Tube           | 50                     | TO220FE-2L (E)  | 21-Dec-2020        |
|              |                 |                       |                |                        | SOD113A (A)     | 10-April-2014      |

# 7. Marking

### **Table 4. Marking codes**

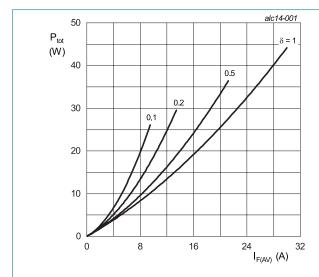
| Type number  | Marking codes                 |                               |  |
|--------------|-------------------------------|-------------------------------|--|
|              | Assembly factory: E           | Assembly factory: A           |  |
| BYC30X-600PS | BYC30X<br>600PS<br>PJExxxx xx | BYC30X<br>600PS<br>PJAxxxx xx |  |

# 8. Limiting values

#### **Table 5. Limiting values**

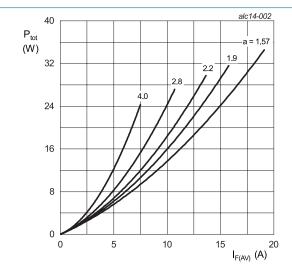
In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol             | Parameter                           | Conditions  | Values     | Unit |
|--------------------|-------------------------------------|---|------------|------|
| $V_{RRM}$          | repetitive peak reverse voltage     |   | 600        | V    |
| $V_{RWM}$          | crest working reverse voltage       |   | 600        | V    |
| $V_R$              | reverse voltage                     | DC  | 600        | V    |
| I <sub>F(AV)</sub> | average forward current             | $δ = 0.5$ ; square-wave pulse; $T_h \le 51$ °C;<br>Fig. 1; Fig. 2; Fig. 3 | 30         | А    |
| I <sub>FRM</sub>   | repetitive peak forward current     | $δ = 0.5$ ; $t_p = 25 \mu s$ ; $T_h \le 51 °C$ ; square-wave pulse        | 60         | А    |
| I <sub>FSM</sub>   | non-repetitive peak forward current | $t_p$ = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse;<br>Fig. 4          | 260        | А    |
|                    |                                     | $t_p$ = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse                    | 286        | А    |
| T <sub>stg</sub>   | storage temperature                 |   | -65 to 175 | °C   |
| T <sub>j</sub>     | junction temperature                |   | -65 to 175 | °C   |



 $I_{F(AV)} = I_{F(RMS)} \times \sqrt{\delta}$   $V_o = 0.883 \text{ V; } R_s = 0.0197\Omega$ 

Fig. 1. Forward power dissipation as a function of average forward current; square waveform; maximum values



a = form factor =  $I_{F(RMS)}/I_{F(AV)}$  $V_o$  = 0.883 V;  $R_s$  = 0.0197 $\Omega$ 

Fig. 2. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values

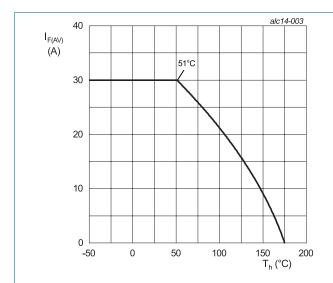


Fig. 3. Forward current as a function of heatsink temperature; maximum values

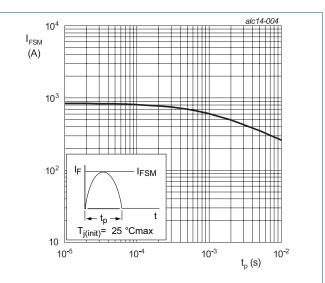
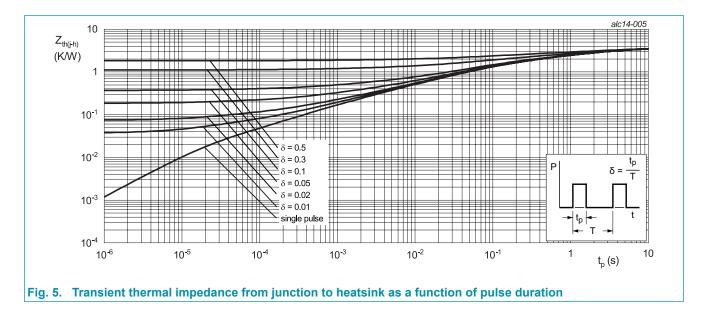


Fig. 4. Non-repetitive peak forward current as a function of pulse width; sinusoidal waveform; maximum values

### 9. Thermal characteristics

**Table 6. Thermal characteristics** 

| Symbol               | Parameter  | Conditions  | Min | Тур | Max | Unit |
|----------------------|--|-------------|-----|-----|-----|------|
| $R_{\text{th(j-c)}}$ | thermal resistance from junction to case                   |             | -   | -   | 3   | K/W  |
| R <sub>th(c-h)</sub> | thermal resistance from case to heatsink                   |             | -   | -   | 0.5 | K/W  |
| $R_{\text{th(j-a)}}$ | thermal resistance<br>from junction to<br>ambient free air | in free air | -   | 55  | -   | K/W  |



### 10. Isolation characteristics

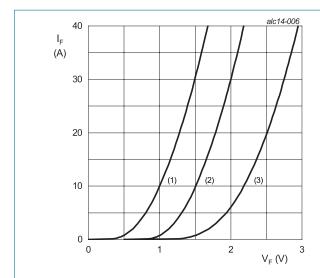
**Table 7. Isolation characteristics** 

| Symbol                 | Parameter             | Conditions   | Min | Тур | Max  | Unit |
|------------------------|-----------------------|--|-----|-----|------|------|
| V <sub>isol(RMS)</sub> | RMS isolation voltage | 50 Hz ≤ f ≤ 60 Hz; RH ≤ 65 %; from all pins to external heatsink; sinusoidal waveform; clean and dust free | -   | -   | 2500 | V    |
| C <sub>isol</sub>      | isolation capacitance | f = 1 MHz; from cathode to external heatsink   | -   | 10  | -    | PF   |

## 11. Characteristics

Table 8 Characteristics

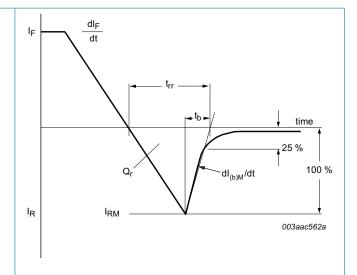
| Symbol                     | Parameter                     | Conditions   | Min | Тур  | Max  | Unit |
|----------------------------|-------------------------------|--|-----|------|------|------|
| Static cha                 | racteristics                  |  | '   | '    |      |      |
| $V_{F}$                    | forward voltage               | I <sub>F</sub> = 30 A; T <sub>j</sub> = 25 °C; <u>Fig. 6</u>   | -   | 2    | 2.75 | V    |
|                            |                               | I <sub>F</sub> = 30 A; T <sub>j</sub> = 150 °C; <u>Fig. 6</u>  | -   | 1.5  | 2    | V    |
| I <sub>R</sub>             | reverse current               | V <sub>R</sub> = 600 V; T <sub>j</sub> = 25 °C   | -   | -    | 10   | μA   |
|                            |                               | V <sub>R</sub> = 600 V; T <sub>j</sub> = 150 °C  | -   | -    | 600  | μA   |
| Dynamic                    | characteristics               |  | '   |      |      |      |
| t <sub>rr</sub> reverse re | reverse recovery time         | $I_F = 1 \text{ A; } V_R = 30 \text{ V; } dI_F/dt = 50 \text{ A/}\mu\text{s;}$<br>$T_j = 25 \text{ °C; } Fig. 7$       | -   | -    | 45   | ns   |
|                            |                               | $I_F = 30 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A/}\mu\text{s};$<br>$T_j = 25 \text{ °C}; Fig. 7$       | -   | 51   | -    | ns   |
|                            |                               | $I_F = 30 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A/}\mu\text{s};$<br>$T_j = 125 \text{ °C}; Fig. 7$      | -   | 105  | -    | ns   |
| I <sub>RM</sub>            | peak reverse recovery current | $I_F = 30 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A/}\mu\text{s};$<br>$T_j = 25 \text{ °C}; Fig. 7$       | -   | 3.7  | -    | А    |
|                            |                               | $I_F = 30 \text{ A}$ ; $V_R = 200 \text{ V}$ ; $dI_F/dt = 200 \text{ A/}\mu\text{s}$ ; $T_j = 125 \text{ °C}$ ; Fig. 7 | -   | 9.5  | -    | А    |
| Q <sub>r</sub>             | recovered charge              | $I_F = 30 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A/µs};$<br>$T_j = 25 \text{ °C}; Fig. 7$                | -   | 95   | -    | nC   |
|                            |                               | $I_F = 30 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A/µs};$<br>$T_j = 125 \text{ °C}; Fig. 7$               | -   | 498  | -    | nC   |
| S <sub>factor</sub>        | softness factor               | $I_F = 30 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A/}\mu\text{s};$<br>$T_i = 125 \text{ °C}; Fig. 7$      | -   | 0.55 | -    |      |



 $V_o = 0.883$  V;  $R_s = 0.0197\Omega$ (1)  $T_j = 150$  °C; typical values (2)  $T_j = 150$  °C; maximum values

(3) T<sub>i</sub> = 25 °C; maximum values

Fig. 6. Forward current as a function of forward voltage

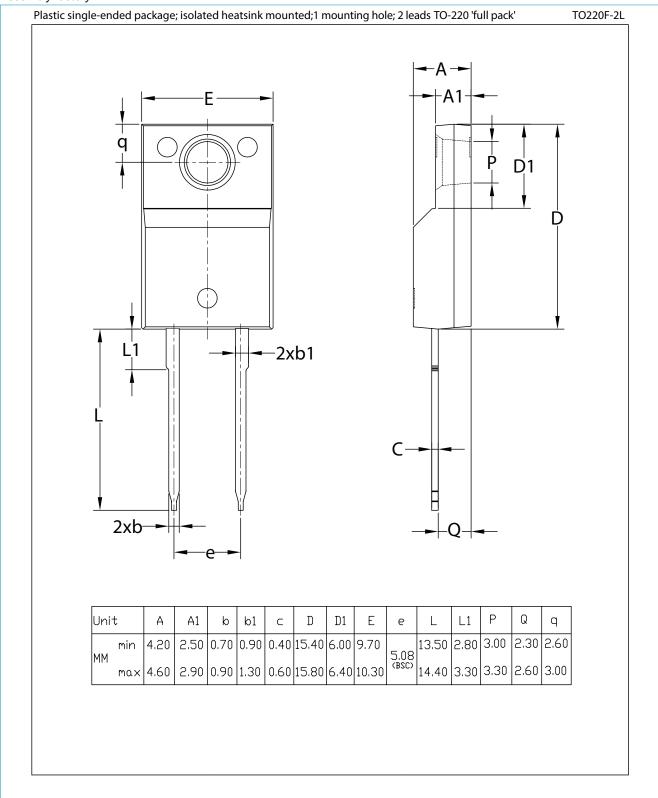


 $S_{factor} = [dI_F/dt] / [dI_{(b)M}/dt]$  $dI_{(b)M}/dt$  = peak rate of change of current during  $t_b$ portion of t<sub>rr</sub>

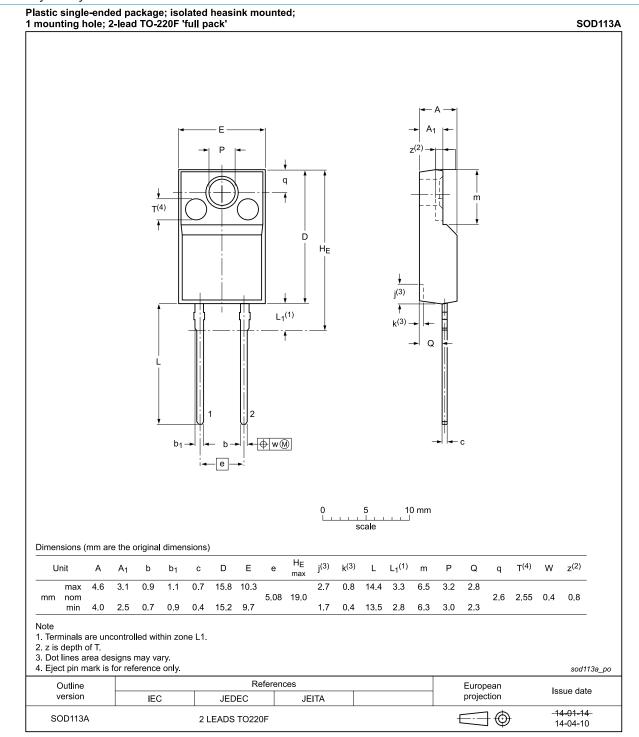
Fig. 7. Reverse recovery definitions; ramp recovery

# 12. Package outline

Assembly factory: E



#### Assembly factory: A



### 13. Legal information

#### Data sheet status

| Document status [1][2]               | Product status [3] | Definition  |
|--------------------------------------|--------------------|---|
| Objective<br>[short] data<br>sheet   | Development        | This document contains data from the objective specification for product development. |
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**BYC30X-600PS** 

Hyperfast power diode

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## 14. Contents

| 1. General description        | 1 |
|-------------------------------|---|
| 2. Features and benefits      | 1 |
| 3. Applications               | 1 |
| 4. Quick reference data       | 1 |
| 5. Pinning information        | 2 |
| 6. Ordering information       | 2 |
| 7. Marking                    | 2 |
| 8. Limiting values            | 3 |
| 9. Thermal characteristics    | 5 |
| 10. Isolation characteristics | 5 |
| 11. Characteristics           | 6 |
| 12. Package outline           | 7 |
| 13. Legal information         |   |
| 14. Contents                  |   |

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